

FEATURES

- <0.5 pC charge injection over full signal range
- 2.5 pF off capacitance
- Low leakage; 0.6 nA maximum @ 85°C
- 120 Ω on resistance
- Fully specified at +12 V, ±15 V
- No V_L supply required
- 3 V logic-compatible inputs
- Rail-to-rail operation
- 8-lead SOT-23 package

APPLICATIONS

- Automatic test equipment
- Data acquisition systems
- Battery-powered systems
- Sample-and-hold systems
- Audio/video signal routing
- Communication systems

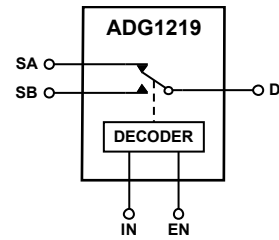
GENERAL DESCRIPTION

The ADG1219 is a monolithic *i*CMOS® device containing an SPDT switch. An EN input is used to enable or disable the device. When disabled, all channels are switched off. When on, each channel conducts equally well in both directions and has an input signal range that extends to the supplies. Each switch exhibits break-before-make switching action.

The *i*CMOS (industrial CMOS) modular manufacturing process combines high voltage complementary metal-oxide semiconductor (CMOS) and bipolar technologies. It enables the development of a wide range of high performance analog ICs capable of 33 V operation in a footprint that no other generation of high voltage parts has been able to achieve. Unlike analog ICs using conventional CMOS processes, *i*CMOS components can tolerate high supply voltages while providing increased performance, dramatically lower power consumption, and reduced package size.

The ultralow capacitance and exceptionally low charge injection of these multiplexers make them ideal solutions for data acquisition and sample-and-hold applications, where low glitch and fast settling are required. Figure 2 shows that there is minimum

FUNCTIONAL BLOCK DIAGRAM



SWITCHES SHOWN FOR A LOGIC 0 INPUT

Figure 1.

06575-001

charge injection over the entire signal range of the device. *i*CMOS construction also ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

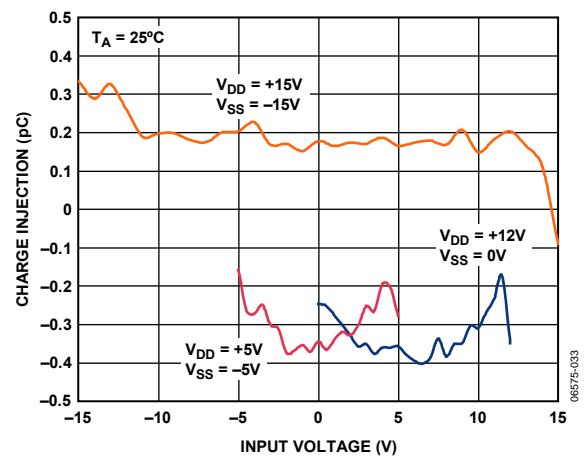


Figure 2. Charge Injection vs. Input Voltage

06575-033

Rev. A

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ADG1219* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

DOCUMENTATION

Application Notes

- AN-874: Operating the ADG12xx Series of Parts with 5 V Supplies and the Impact on Performance

Data Sheet

- ADG1219: Low Capacitance, Low Charge Injection, ± 15 V/12 V μ CMOS SPDT in SOT-23 Data Sheet

REFERENCE MATERIALS

Product Selection Guide

- Switches and Multiplexers Product Selection Guide

DESIGN RESOURCES

- ADG1219 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all ADG1219 EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

Submit feedback for this data sheet.

TABLE OF CONTENTS

Features	1	Absolute Maximum Ratings	6
Applications.....	1	ESD Caution.....	6
Functional Block Diagram	1	Pin Configuration and Function Descriptions.....	7
General Description	1	Typical Performance Characteristics	8
Revision History	2	Test Circuits.....	12
Specifications.....	3	Terminology	14
Dual Supply	3	Outline Dimensions	15
Single Supply	4	Ordering Guide	15

REVISION HISTORY

3/09—Rev. 0 to Rev. A	
Change to Power Requirements, I _{DD} Parameter, Table 1.....	4
Change to Power Requirements, I _{DD} Parameter, Table 2.....	5
Updated Outline Dimensions	15
4/08—Revision 0: Initial Version	

SPECIFICATIONS

DUAL SUPPLY

$V_{DD} = 15\text{ V} \pm 10\%$, $V_{SS} = -15\text{ V} \pm 10\%$, GND = 0 V, unless otherwise noted.

Table 1.

Parameters	B Version ¹			Unit	Test Conditions/Comments
	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance, R_{ON}	120			Ω typ	$V_S = \pm 10\text{ V}$, $I_S = -1\text{ mA}$; see Figure 23 $V_{DD} = +13.5\text{ V}$, $V_{SS} = -13.5\text{ V}$ $V_S = \pm 10\text{ V}$, $I_S = -1\text{ mA}$
	200	240	270	Ω max	
On Resistance Match Between Channels, ΔR_{ON}	3.5			Ω typ	
	6	10	12	Ω max	$V_S = -5\text{ V}$, 0 V, +5 V; $I_S = -1\text{ mA}$
On Resistance Flatness, $R_{FLAT(ON)}$	20			Ω typ	
	64	76	84	Ω max	
LEAKAGE CURRENTS					
Source Off Leakage, I_S (Off)	± 0.004			nA typ	$V_{DD} = +16.5\text{ V}$, $V_{SS} = -16.5\text{ V}$ $V_S = \pm 10\text{ V}$, $V_D = \pm 10\text{ V}$; see Figure 24
	± 0.1	± 0.6	± 1	nA max	
Drain Off Leakage, I_D (Off)	± 0.009			nA typ	$V_S = \pm 10\text{ V}$, $V_D = \pm 10\text{ V}$; see Figure 24
	± 0.1	± 0.6	± 1	nA max	
Channel On Leakage, I_D , I_S (On)	± 0.02			nA typ	$V_S = V_D = \pm 10\text{ V}$; see Figure 25
	± 0.2	± 0.6	± 1	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	$V_{IN} = V_{INL}$ or V_{INH}
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.005			μA typ	
			± 0.1	μA max	
Digital Input Capacitance, C_{IN}	2			pF typ	
DYNAMIC CHARACTERISTICS²					
Transition Time, $t_{TRANSITION}$	140			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 10\text{ V}$; see Figure 30
	170	200	230	ns max	
t_{ON} (EN)	85			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 10\text{ V}$; see Figure 30
	105	130	140	ns max	
t_{OFF} (EN)	105			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 10\text{ V}$; see Figure 30
	125	150	170	ns max	
Break-Before-Make Time Delay, t_{BBM}	40			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_{S1} = V_{S2} = 10\text{ V}$; see Figure 31
			10	ns min	
Charge Injection	0.1			pC typ	$V_S = 0\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32
Off Isolation	77			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 26
Channel-to-Channel Crosstalk	80			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 27
Total Harmonic Distortion + Noise	0.15			% typ	$R_L = 10\text{ k}\Omega$, 5 V rms, $f = 20\text{ Hz}$ to 20 kHz $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 28
-3 dB Bandwidth	520			MHz typ	
C_S (Off)	2.5			pF typ	$f = 1\text{ MHz}$; $V_S = 0\text{ V}$
	3.3			pF max	$f = 1\text{ MHz}$; $V_S = 0\text{ V}$
C_D (Off)	4.3			pF typ	$f = 1\text{ MHz}$; $V_S = 0\text{ V}$
	5.1			pF max	$f = 1\text{ MHz}$; $V_S = 0\text{ V}$
C_D , C_S (On)	7.5			pF typ	$f = 1\text{ MHz}$; $V_S = 0\text{ V}$
	10			pF max	$f = 1\text{ MHz}$; $V_S = 0\text{ V}$

ADG1219

Parameters	B Version ¹			Unit	Test Conditions/Comments
	25°C	-40°C to +85°C	-40°C to +125°C		
POWER REQUIREMENTS					$V_{DD} = +16.5\text{ V}$, $V_{SS} = -16.5\text{ V}$
I_{DD}	0.001		1.0	$\mu\text{A typ}$ $\mu\text{A max}$	Digital inputs = 0 V or V_{DD}
I_{DD}	140		190	$\mu\text{A typ}$ $\mu\text{A max}$	Digital inputs = 5 V
I_{SS}	0.001		1.0	$\mu\text{A typ}$ $\mu\text{A max}$	Digital inputs = 0 V, 5 V or V_{DD}
V_{DD}/V_{SS}			$\pm 5/\pm 16.5$	V min/max	$ V_{DD} = V_{SS} $

¹ Temperature range for B version is -40°C to +125°C.

² Guaranteed by design; not subject to production test.

SINGLE SUPPLY

$V_{DD} = 12\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $\text{GND} = 0\text{ V}$, unless otherwise noted.

Table 2.

Parameters	B Version ¹			Unit	Test Conditions/Comments
	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance, R_{ON}	300			$\Omega\text{ typ}$	$V_S = 0\text{ V to }10\text{ V}$, $I_S = -1\text{ mA}$; see Figure 23
	475	567	625	$\Omega\text{ max}$	$V_{DD} = 10.8\text{ V}$, $V_{SS} = 0\text{ V}$
On Resistance Match Between Channels, ΔR_{ON}	4.5			$\Omega\text{ typ}$	$V_S = 0\text{ V to }10\text{ V}$, $I_S = -1\text{ mA}$
	16	26	27	$\Omega\text{ max}$	
On Resistance Flatness, $R_{FLAT(ON)}$	60			$\Omega\text{ typ}$	$V_S = 3\text{ V, }6\text{ V, }9\text{ V}$, $I_S = -1\text{ mA}$
LEAKAGE CURRENTS					$V_{DD} = 13.2\text{ V}$
Source Off Leakage, I_S (Off)	± 0.006			nA typ	$V_S = 1\text{ V}/10\text{ V}$, $V_D = 10\text{ V}/1\text{ V}$; see Figure 24
	± 0.1	± 0.6	± 1	nA max	
Drain Off Leakage, I_D (Off)	± 0.006			nA typ	$V_S = 1\text{ V}/10\text{ V}$, $V_D = 10\text{ V}/1\text{ V}$; see Figure 24
	± 0.1	± 0.6	± 1	nA max	
Channel On Leakage, I_D , I_S (On)	± 0.02			nA typ	$V_S = V_D = 1\text{ V or }10\text{ V}$; see Figure 25
	± 0.2	± 0.6	± 1	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.001			$\mu\text{A typ}$ $\mu\text{A max}$	$V_{IN} = V_{INL}$ or V_{INH}
			± 0.1	$\mu\text{A max}$	
Digital Input Capacitance, C_{IN}	3			pF typ	
DYNAMIC CHARACTERISTICS ²					
Transition Time, $t_{TRANSITION}$	195			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	250	300	340	ns max	$V_S = 8\text{ V}$; see Figure 30
t_{ON} (EN)	120			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	150	190	210	ns max	$V_S = 8\text{ V}$; see Figure 30
t_{OFF} (EN)	145			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	185	220	255	ns max	$V_S = 8\text{ V}$; see Figure 30
Break-Before-Make Time Delay, t_{BBM}	70			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
			10	ns min	$V_{S1} = V_{S2} = 8\text{ V}$; see Figure 31
Charge Injection	-0.8			pC typ	$V_S = 6\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32
Off Isolation	80			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 26
Channel-to-Channel Crosstalk	80			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 27
-3 dB Bandwidth	400			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 28

Parameters	B Version ¹			Unit	Test Conditions/Comments
	25°C	-40°C to +85°C	-40°C to +125°C		
C _S (Off)	2.9			pF typ	f = 1 MHz; V _S = 6 V
	3.7			pF max	f = 1 MHz; V _S = 6 V
C _D (Off)	5			pF typ	f = 1 MHz; V _S = 6 V
	5.8			pF max	f = 1 MHz; V _S = 6 V
C _D , C _S (On)	8.5			pF typ	f = 1 MHz; V _S = 6 V
	11			pF max	f = 1 MHz; V _S = 6 V
POWER REQUIREMENTS					V _{DD} = 13.2 V
I _{DD}	0.001		1.0	μA typ	Digital inputs = 0 V or V _{DD}
				μA max	
I _{DD}	140		190	μA typ	Digital inputs = 5 V
				μA max	
V _{DD}			5/16.5	V min/max	V _{SS} = 0 V, GND = 0 V

¹ Temperature range for B version is -40°C to +125°C.

² Guaranteed by design; not subject to production test.

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted.

Table 3.

Parameter	Rating
V _{DD} to V _{SS}	35 V
V _{DD} to GND	−0.3 V to +25 V
V _{SS} to GND	+0.3 V to −25 V
Analog Inputs ¹	V _{SS} − 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first
Digital Inputs ¹	GND − 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first
Peak Current, S or D	100 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current per Channel, S or D	30 mA
Operating Temperature Range Industrial (B Version)	−40°C to +125°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
8-Lead SOT-23, θ _{JA} Thermal Impedance	211.5°C/W
Reflow Soldering Peak Temperature, Pb Free	260°C

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

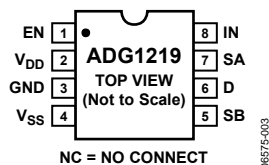


Figure 3. SOT-23 Pin Configuration

Table 4. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	EN	Active High Digital Input. When this pin is low, the device is disabled and all switches are turned off. When this pin is high, the IN logic input determines which switch is turned on.
2	V _{DD}	Most Positive Power Supply Potential.
3	GND	Ground (0 V) Reference.
4	V _{SS}	Most Negative Power Supply Potential.
5	SB	Source Terminal. Can be an input or output.
6	D	Drain Terminal. Can be an input or output.
7	SA	Source Terminal. Can be an input or output.
8	IN	Logic Control Input.

Table 5. Truth Table

EN	IN	Switch A	Switch B
0	X	Off	Off
1	0	On	Off
1	1	Off	On

TYPICAL PERFORMANCE CHARACTERISTICS

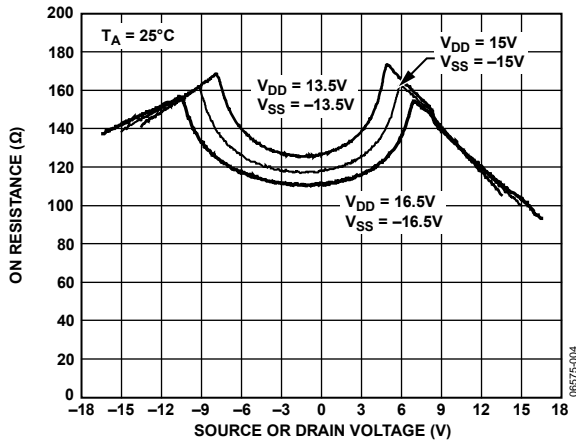


Figure 4. On Resistance as a Function of V_D (V_S) for Dual Supply

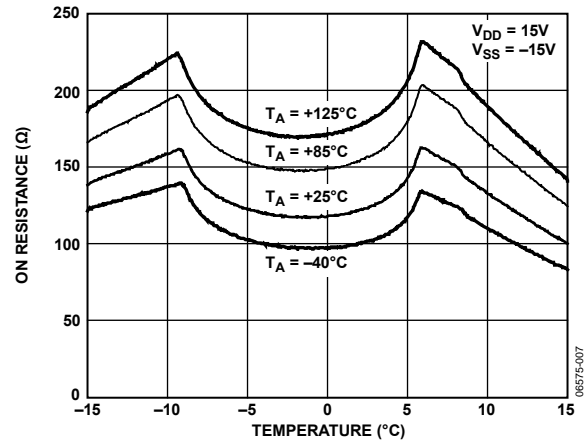


Figure 7. On Resistance as a Function of V_D (V_S) for Different Temperatures, Dual Supply

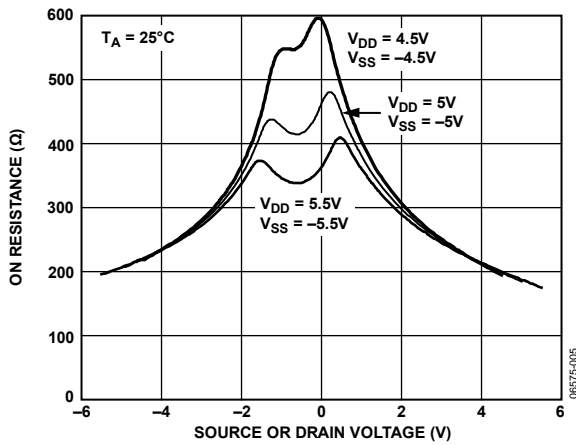


Figure 5. On Resistance as a Function of V_D (V_S) for Dual Supply

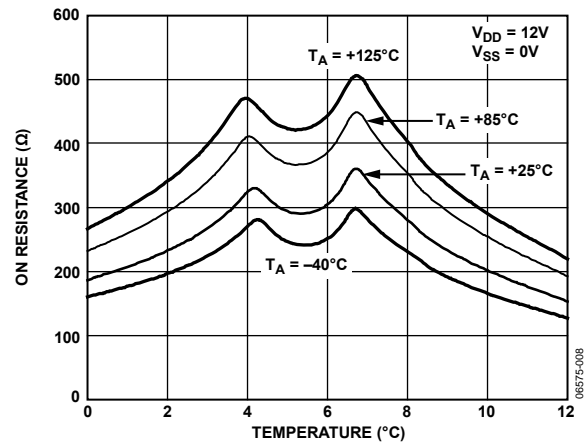


Figure 8. On Resistance as a Function of V_D (V_S) for Different Temperatures, Single Supply

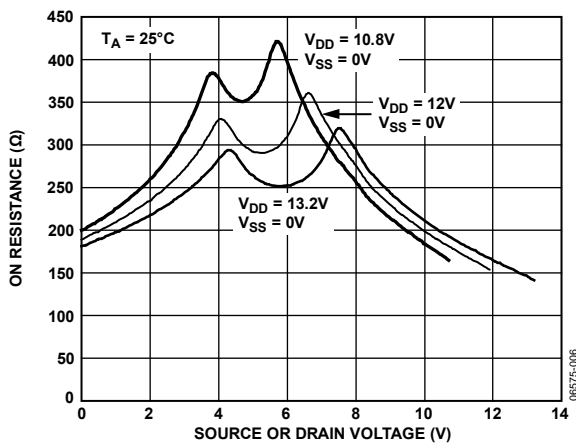


Figure 6. On Resistance as a Function of V_D (V_S) for Single Supply

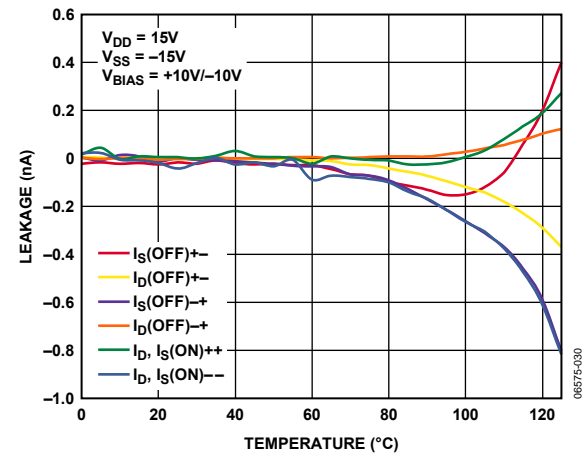


Figure 9. Leakage Currents as a Function of Temperature, 15 V Dual Supply

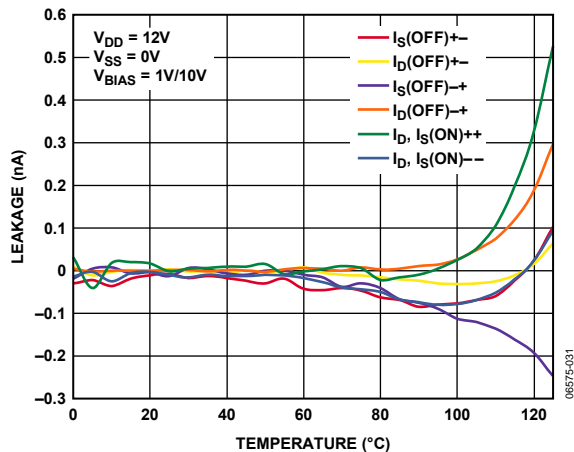


Figure 10. Leakage Currents as a Function of Temperature, 12 V Single Supply

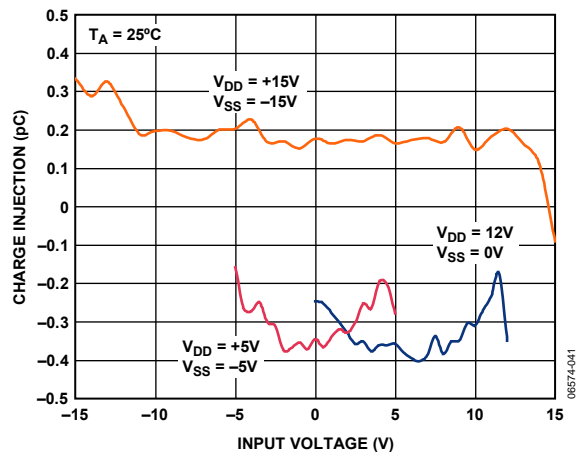


Figure 13. Charge Injection vs. Input Voltage

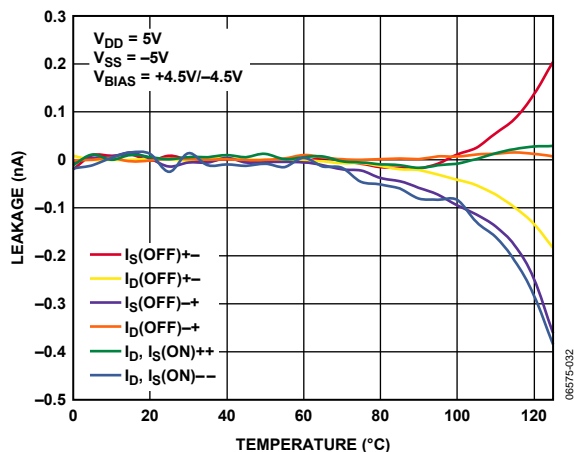


Figure 11. Leakage Currents as a Function of Temperature, 5 V Dual Supply

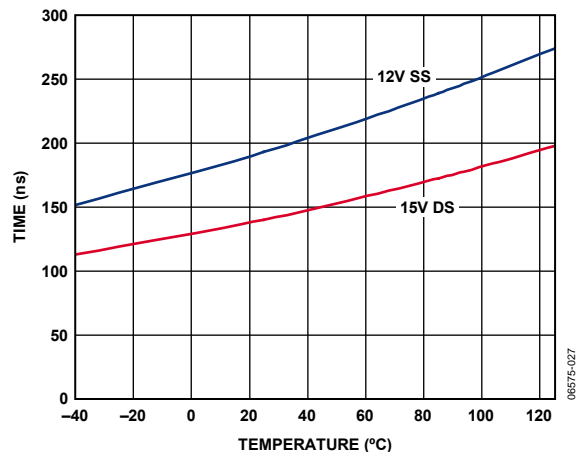


Figure 14. $t_{\text{TRANSITION}}$ Time vs. Temperature

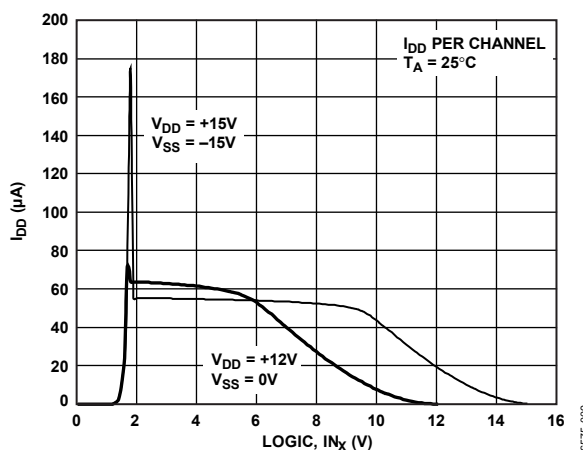


Figure 12. I_{DD} vs. Logic Level

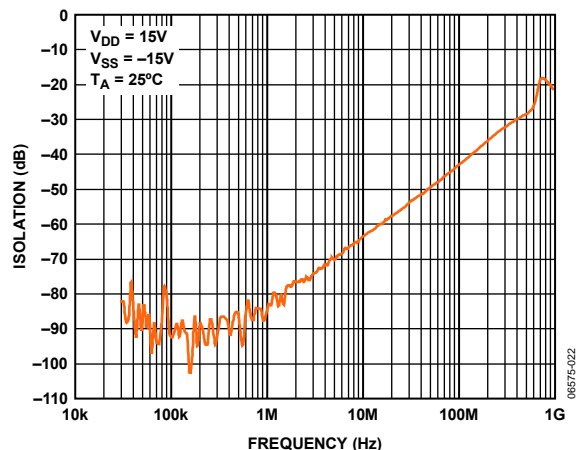


Figure 15. Off Isolation vs. Frequency

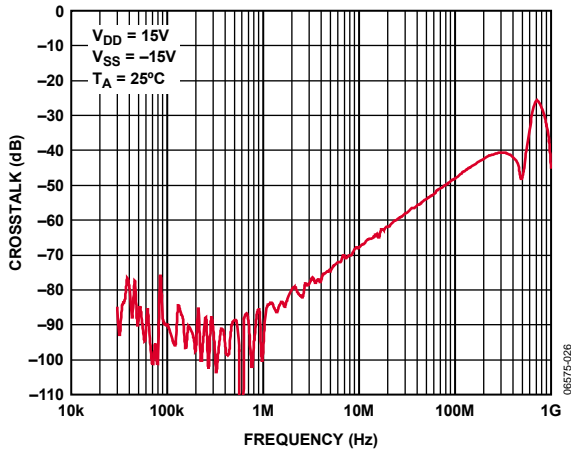


Figure 16. Crosstalk vs. Frequency

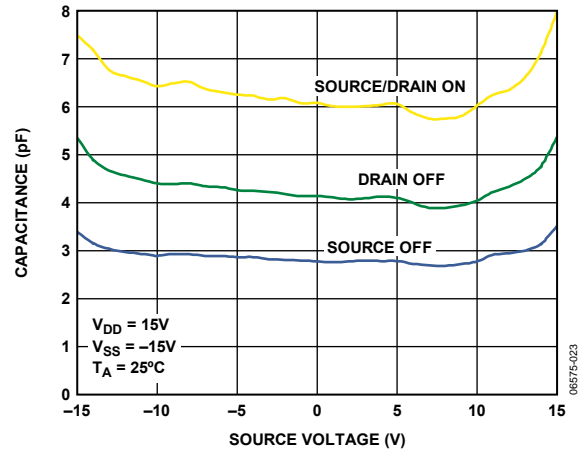


Figure 19. Capacitance vs. Source Voltage for Dual Supply

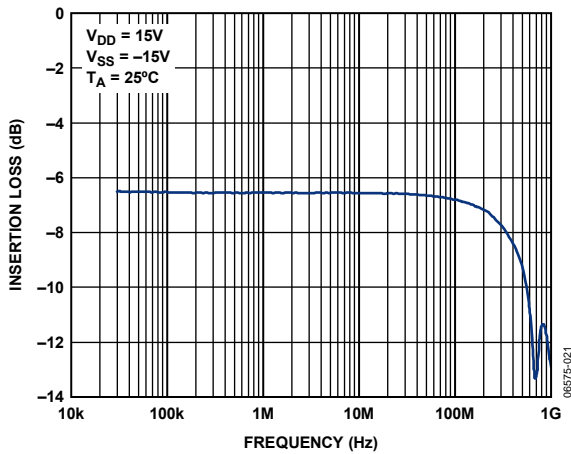


Figure 17. On Response vs. Frequency

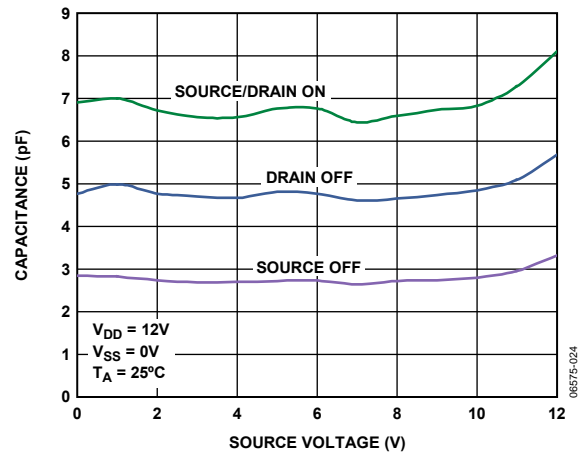


Figure 20. Capacitance vs. Source Voltage for Single Supply

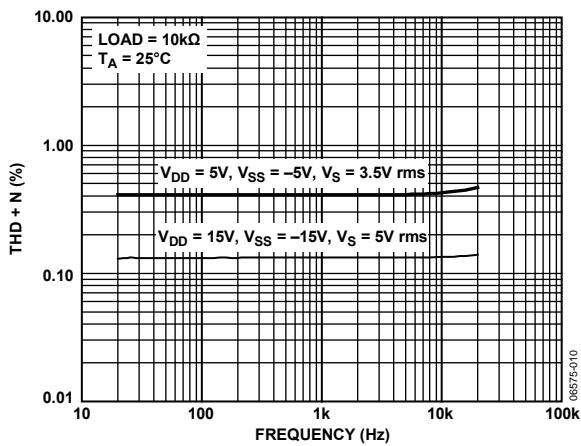


Figure 18. THD + N vs. Frequency

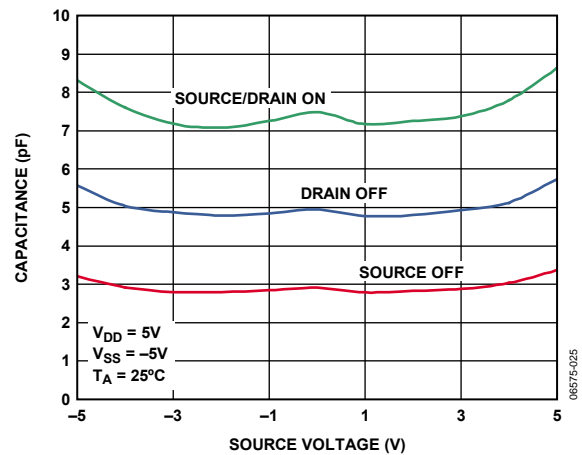


Figure 21. Capacitance vs. Source Voltage for Dual Supply

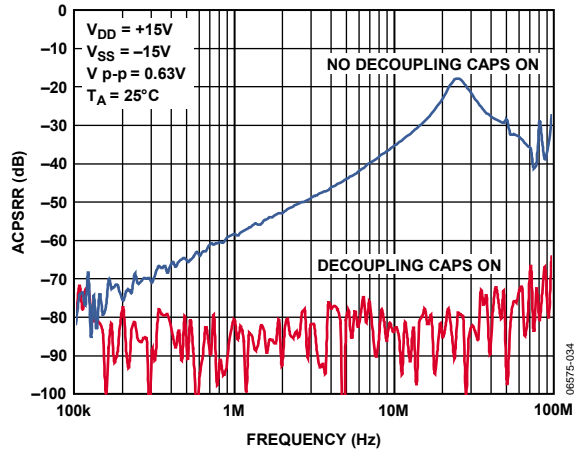


Figure 22. ACPSRR vs. Frequency

TEST CIRCUITS

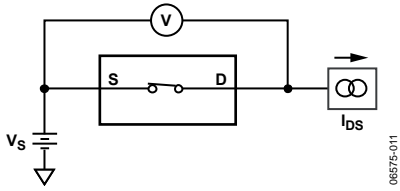


Figure 23. On Resistance

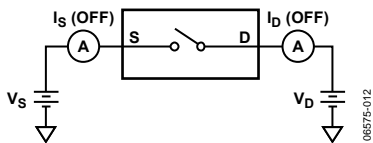


Figure 24. Off Leakage

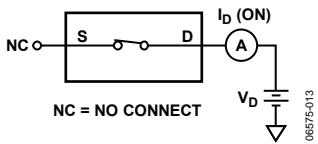


Figure 25. On Leakage

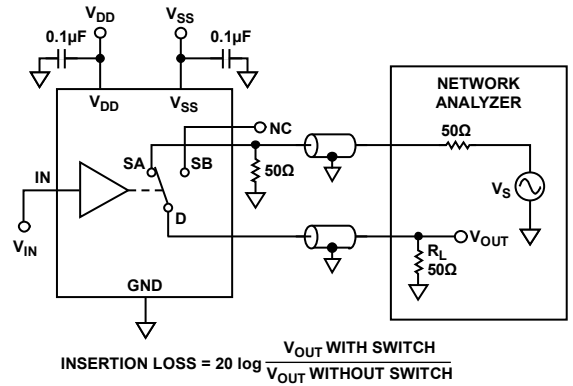


Figure 27. Channel-to-Channel Crosstalk

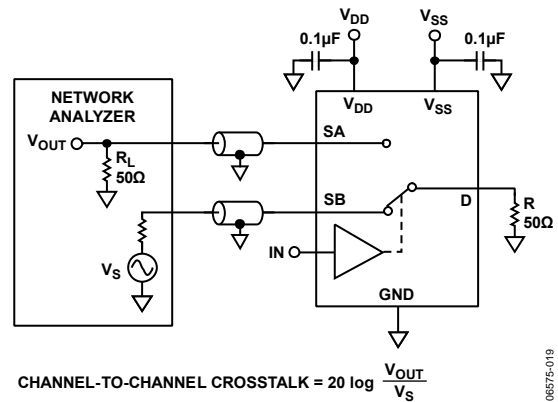


Figure 28. Bandwidth

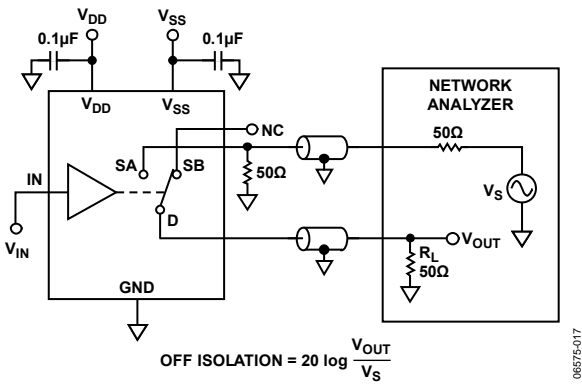


Figure 26. Off Isolation

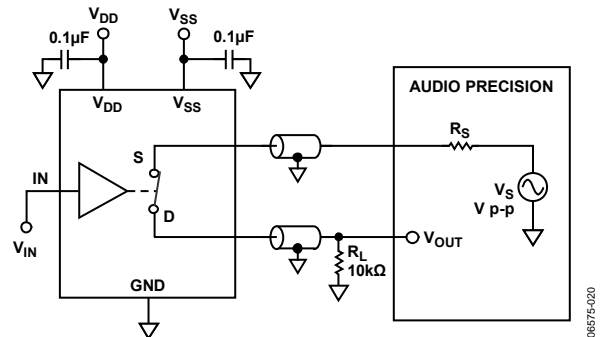


Figure 29. THD + Noise

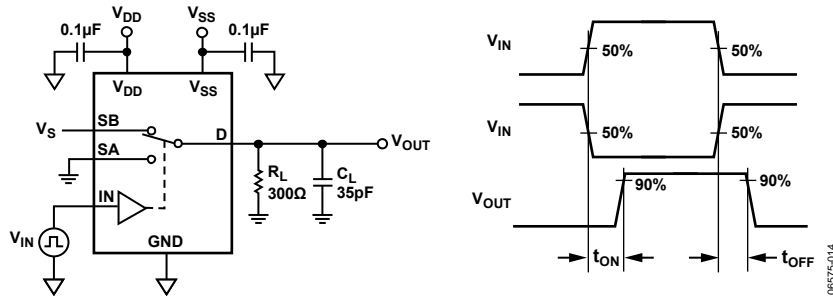


Figure 30. Switching Times

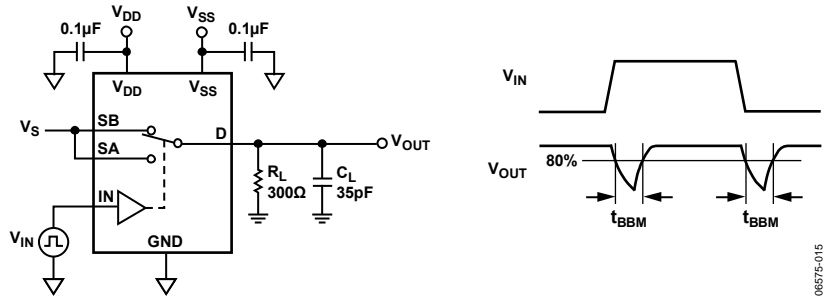


Figure 31. Break-Before-Make Time Delay

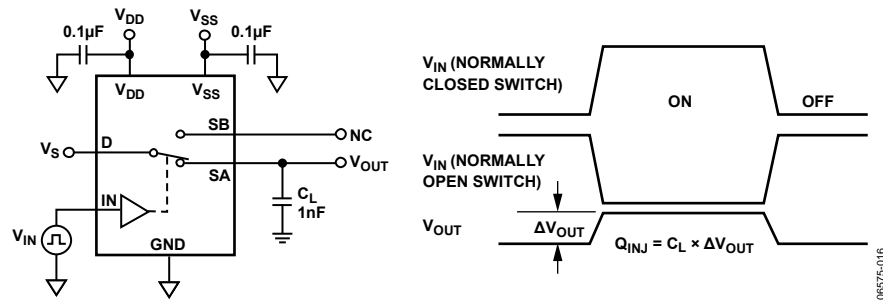


Figure 32. Charge Injection

TERMINOLOGY

I_{DD}

The positive supply current.

I_{SS}

The negative supply current.

V_D (V_S)

The analog voltage on Terminal D and Terminal S.

R_{ON}

The ohmic resistance between Terminal D and Terminal S.

R_{FLAT(ON)}

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

I_S (Off)

The source leakage current with the switch off.

I_D (Off)

The drain leakage current with the switch off.

I_D, I_S (On)

The channel leakage current with the switch on.

V_{INL}

The maximum input voltage for Logic 0.

V_{INH}

The minimum input voltage for Logic 1.

I_{INL} (I_{INH})

The input current of the digital input.

C_S (Off)

The off switch source capacitance, measured with reference to ground.

C_D (Off)

The off switch drain capacitance, measured with reference to ground.

C_D, C_S (On)

The on switch capacitance, measured with reference to ground.

C_{IN}

The digital input capacitance.

t_{ON} (EN)

Delay time between the 50% and 90% points of the digital input and switch on condition.

t_{OFF} (EN)

Delay time between the 50% and 90% points of the digital input and switch off condition.

t_{TRANSITION}

Delay time between the 50% and 90% points of the digital inputs and the switch on condition when switching from one address state to another.

T_{BBM}

Off time measured between the 80% point of both switches when switching from one address state to another.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

Insertion Loss

The loss due to the on resistance of the switch.

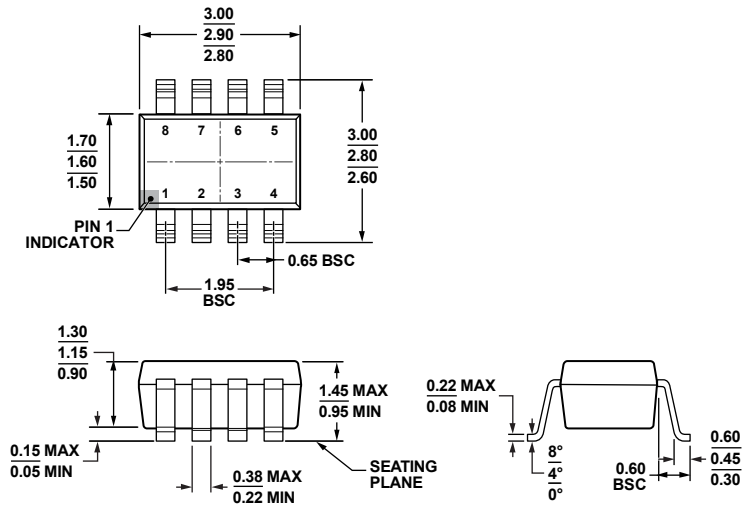
Total Harmonic Distortion (THD + N)

The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

AC Power Supply Rejection Ratio (ACPSRR)

Measures the ability of a part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p. The ratio of the amplitude of signal on the output to the amplitude of the modulation is the ACPSRR.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-178-BA

Figure 33. 8-Lead Lead Small Outline Transistor Package [SOT-23] (RJ-8)

Dimensions shown in millimeters

121608-A

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
ADG1219BRJZ-R2 ¹	-40°C to +125°C	8-Lead Lead Small Outline Transistor Package [SOT-23]	RJ-8	S24
ADG1219BRJZ-REEL7 ¹	-40°C to +125°C	8-Lead Lead Small Outline Transistor Package [SOT-23]	RJ-8	S24

¹ Z = RoHS Compliant Part.

ADG1219

NOTES